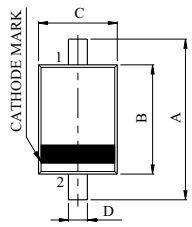
KDV348E

VARIABLE CAPACITANCE DIODE
SILICON EPITAXIAL PLANAR DIODE

VCO.

FEATURES

- Low Series Resistance : r_S=0.50Ω(Max.)
- Small Package.



DIM	MILLIMETERS
A	1.60±0.10
B	1.20±0.10
C	0.80±0.10
D	0.30±0.05
E	0.60±0.10
F	0.13±0.05

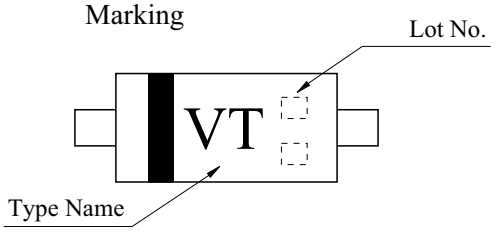
1. ANODE
2. CATHODE

ESC

MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Reverse Voltage	V_R	10	V
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55 150	℃
Forward Current	I_F	20	mA

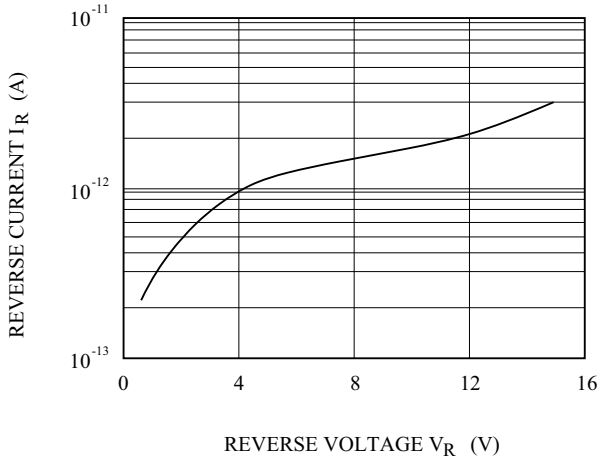
Marking



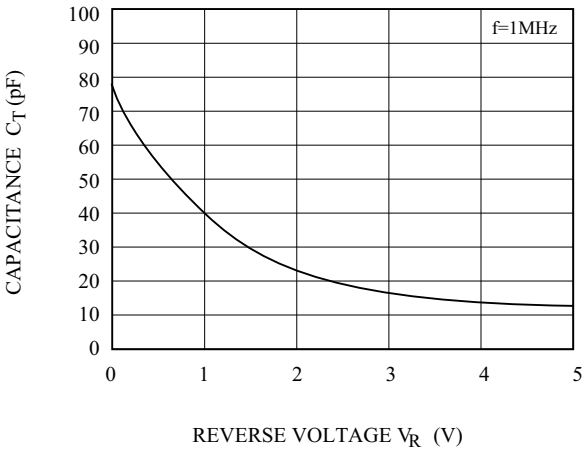
ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Reverse Voltage	V_R	I_R=1 μA	10	-	-	V
Reverse Current	I_R	V_R=6V	-	-	10	nA
		V_R=6V, T_A=85℃	-	-	100	
Capacitance	C_{1V}	V_R=1V, f=1MHz	37	40	44	pF
	C_{2V}	V_R=2V, f=1MHz	21	-	26	
	C_{3V}	V_R=3V, f=1MHz	14	15.8	17.6	
	C_{4V}	V_R=4V, f=1MHz	-	12.1	-	
Capacitance Ratio	C_{1V}/C_{3V}	f=1MHz	2.15	2.53	-	-
	C_{1V}/C_{4V}	f=1MHz	-	3.3	-	-
Series Resistance	r_S	V_R=1V, f=470MHz	-	0.25	0.5	Ω

I_R - V_R



C_T - V_R



r_s - V_R

